

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	IS&R	L1	10	(("5875020") or ("5663582") or ("5895956") or ("6130461") or ("5204274") or ("5318917") or ("5693964") or ("6010955") or ("4814854") or ("4931411")).PN.	USPAT; US-PGPUB	2002/05/13 14:27
2	IS&R	L2	40	(("5376812") or ("5439846") or ("5555044") or ("5555043") or ("5643811") or ("5668065") or ("5793114") or ("4811078") or ("4868137") or ("4984055") or ("5334860") or ("5485019") or ("5519464") or ("5624582") or ("5627384") or ("5641692") or ("5658806") or ("5733804") or ("5804476") or ("5808346") or ("5818550") or ("5849611") or ("5888855") or ("5894139") or ("5897344") or ("5897377") or ("5899739") or ("5926735") or ("5943107") or ("5946240") or ("5953583") or ("6016174") or	USPAT; US-PGPUB	2002/05/13 14:28
3	BRS	L5	7	("5110763" "5200358" "5432381" "5482894" "5498571" "5506177" "5899739").PN.	USPAT	2002/05/13 14:30
4	IS&R	L16	822	(438/586).CCLS.	USPAT; US-PGPUB	2002/05/13 14:42
5	BRS	L17	30	16 and ((non adj volatile) or nonvolatile)	USPAT; US-PGPUB	2002/05/13 14:46
6	IS&R	L18	531	(257/390).CCLS.	USPAT; US-PGPUB	2002/05/13 14:46
7	BRS	L19	100	18 and ((non adj volatile) or nonvolatile)	USPAT; US-PGPUB	2002/05/13 14:50
8	IS&R	L20	1026	(257/751,760).CCLS.	USPAT; US-PGPUB	2002/05/13 14:50
9	BRS	L21	38	20 and ((non adj volatile) or nonvolatile)	USPAT; US-PGPUB	2002/05/13 14:50

	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Inventor
1	US 5731242 A	19980324	15	Self-aligned contact process in semiconductor fabrication	438/586	438/211; 438/593; 438/595; 438/637	Parat, Krishna K. et al.
2	US 5661054 A	19970826	12	Method of forming a non-volatile memory array	438/257	438/586; 438/588	Kauffman, Ralph et al.
3	US 5231043 A	19930727	9	Contact alignment for integrated circuits	438/396	216/6; 438/586; 438/639	Chan, Tsiu C. et al.
4	US 5019527 A	19910528	30	Method of manufacturing non-volatile semiconductor memories, in which selective removal of field oxidation film for forming source region and self-adjusted treatment for forming contact portion are simultaneously performed	438/257	438/586	Ohshima, Yoichi et al.

4438/586

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1	US 6162720 A	20001219	25	Semiconductor device and method of manufacturing the same	438/624	438/637; 438/669	Ozaki, Tohru
2	US 6074915 A	20000613	21	Method of making embedded flash memory with salicide and sac structure	438/258	438/655	Chen, Jong et al.
3	US 5946240 A	19990831	14	Nonvolatile semiconductor memory device and method of manufacturing the same	365/185.28	257/316; 257/317; 365/185.05	Hisamune, Yoshiaki
4	US 5668065 A	19970916	7	Process for simultaneous formation of silicide-based self-aligned contacts and local interconnects	438/303	438/649	Lin, Chen-Hsi
5	US 5506177 A	19960409	15	Fabrication process for multilevel interconnections in a semiconductor device	438/624	438/648; 438/650; 438/760; 438/782	Kishimoto, Koji et al.
6	US 5482894 A	19960109	10	Method of fabricating a self-aligned contact using organic dielectric materials	438/623	438/624; 438/639	Havemann, Robert H.